

ABSTRACT OF THE DISCLOSURE

A semiconductor optical device comprises a superlattice contact semiconductor region and a metal electrode. The superlattice contact semiconductor region has a superlattice structure. The superlattice contact semiconductor region includes a II-VI compound semiconductor region and a II-VI compound semiconductor layer. The II-VI compound semiconductor region contains zinc, selenium and tellurium, and the II-VI compound semiconductor layer contains zinc and selenium. The metal electrode is provided on said superlattice contact semiconductor region and the metal electrode is electrically bonded to the first II-VI compound semiconductor layer.

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